Unit: mm

2SB1537

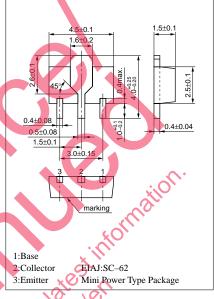
Silicon PNP epitaxial planer type

For low-frequency amplification Complementary to 2SD2357

Features

- Low collector to emitter saturation voltage $V_{CE(sat)}$.
- Large collector power dissipation P_C.
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

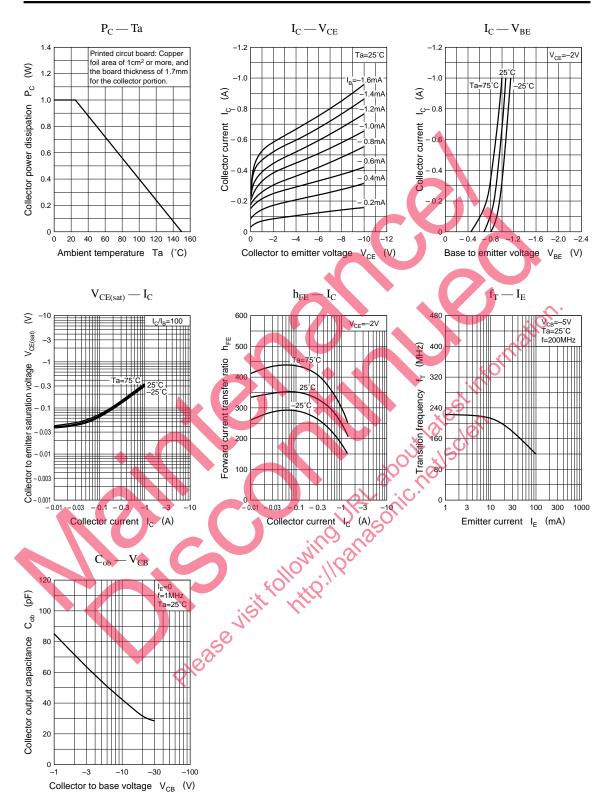
Absolute Maximu	m Ratings	(Ta=25°C)	
Parameter	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	-10	V
Collector to emitter voltage	V _{CEO}	-10	V
Emitter to base voltage	V _{EBO}	-5	v
Peak collector current	I _{CP}	-1.2	А
Collector current	I _C	-1	A
Collector power dissipation	P _c *	1	W
Junction temperature	Tj	150	°C
Storage temperature	T _{stg}	-55 ~ +150	°C



Electrical Characteristics (Ta=25°C

Peak collector current I _C	-1	A 2:Collector EIAJ:SC-62									
Collector current I _C	Y C	1	3:Emitter Mini Power Type Package								
Collector power dissipation P _C	Pc 1 W Marking symbol : 1L										
Junction temperature	1:	50	°C	,00	y's						
Storage temperature T _{st}	g –55 ~	+150	°C	2 v							
Collector power dissipation P_C^* 1 W Marking symbol: 1L Junction temperature T_j 150 °C Storage temperature T_{stg} $-55 \sim +150$ °C * Printed circuit board: Copper foil area of 1cm ² or more, and the board thickness of 1.7mm for the collector portion He board He board Electrical Characteristics (Ta=25°C) Image: Collector portion Image: Collector portion Collector portion											
Parameter	Symbol		Conditions		min	typ	max	Unit			
Collector cutoff current	I _{CBO}	$V_{CB} = -2$	$V, I_E = 0$				-1	μA			
Collector to base voltage	V _{CBO}	$I_{\rm C} = -10$	μ A, I _E = 0		-10			V			
Collector to emitter voltage	V _{CEO}	$I_{\rm C} = -1 \mathrm{mA}, I_{\rm B} = 0$		-10			V				
Emitter to base voltage	V _{EBO}	$I_{\rm E} = -10 \mu A, I_{\rm C} = 0$		-5			v				
Forward current transfer ratio	U FE	$V_{CE} = -2V, I_C = -100mA^{**}$		200		800					
Collector to emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -500 {\rm mA}, I_{\rm B} = -5 {\rm mA}^{**}$				- 0.15	V				
Transition frequency	f _T	$V_{CB} = -5V$, $I_E = 50mA$, $f = 200MHz$			120		MHz				
Collector output capacitance	C _{ob}	$V_{CB} = -\xi$	5V, $I_E = 0$, $f = 1M$	Hz		45		pF			

** Pulse measurement



Request for your special attention and precautions in using the technical information and semiconductors described in this book

- (1) If any of the products or technical information described in this book is to be exported or provided to non-residents, the laws and regulations of the exporting country, especially, those with regard to security export control, must be observed.
- (2) The technical information described in this book is intended only to show the main characteristics and application circuit examples of the products, and no license is granted under any intellectual property right or other right owned by our company or any other company. Therefore, no responsibility is assumed by our company as to the infringement upon any such right owned by any other company which may arise as a result of the use of technical information described in this book.
- (3) The products described in this book are intended to be used for standard applications or general electronic equipment (such as office equipment, communications equipment, measuring instruments and household appliances).
 - Consult our sales staff in advance for information on the following applications:
 - · Special applications (such as for airplanes, aerospace, automobiles, traffic control equipment, combustion equipment, life support systems and safety devices) in which exceptional quality and reliability are required, or if the failure or malfunction of the products may directly jeopardize life or harm the human body.
 - Any applications other than the standard applications intended.
- (4) The products and product specifications described in this book are subject to change without notice for modification and/or improvement. At the final stage of your design, purchasing, or use of the products, therefore, ask for the most up-to-date Product Standards in advance to make sure that the latest specifications satisfy your requirements.
- (5) When designing your equipment, comply with the range of absolute maximum rating and the guaranteed operating conditions (operating power supply voltage and operating environment etc.). Especially, please be careful not to exceed the range of absolute maximum rating on the transient state, such as power-on, power-off and mode-switching. Otherwise, we will not be liable for any defect which may arise later in your equipment.
 - Even when the products are used within the guaranteed values, take into the consideration of incidence of break down and failure mode, possible to occur to semiconductor products. Measures on the systems such as redundant design, arresting the spread of fire or preventing glitch are recommended in order to prevent physical injury, fire, social damages, for example, by using the products.
- (6) Comply with the instructions for use in order to prevent breakdown and characteristics change due to external factors (ESD, EOS, thermal stress and mechanical stress) at the time of handling, mounting or at customer's process. When using products for which damp-proof packing is required, satisfy the conditions, such as shelf life and the elapsed time since first opening the packages.
- , the provention of the providence of the provid (7) This book may be not reprinted or reproduced whether wholly or partially, without the prior written permission of Matsushita Electric Industrial Co., Ltd.